

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
MAGRI' ET AL.)

Serial No. NOT YET ASSIGNED)

Filing Date: HEREWITH)

For: VERTICAL-CONDUCTION AND)
PLANAR-STRUCTURE MOS DEVICE))
WITH A DOUBLE THICKNESS OF)
GATE OXIDE AND METHOD)
REALIZING POWER VERTICAL)
MOS TRANSISTORS WITH)
IMPROVED STATIC AND DYNAMIC))
PERFORMANCES AND HIGH)
SCALING DOWN DENSITY)
)

I HEREBY CERTIFY THIS PAPER OR FEE IS BEING
DEPOSITED WITH THE U.S. POSTAL SERVICE
"EXPRESS MAIL POST OFFICE TO ADDRESSEE"
SERVICE UNDER 37 CFR 1.10 ON THE DATE
INDICATED BELOW AND IS ADDRESSED TO: MAIL
STOP PATENT APPLICATIONS, P.O. BOX 1450,
ALEXANDRIA, VA 22313-1450.

EXPRESS MAIL NO: EV322694470US

DATE OF DEPOSIT: December 30, 2003

NAME: Justin Goree

SIGNATURE: 

PRELIMINARY AMENDMENT

MS Patent Application
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Prior to the calculation of fees and examination of
the present application, please enter the amendments and
remarks set out below.